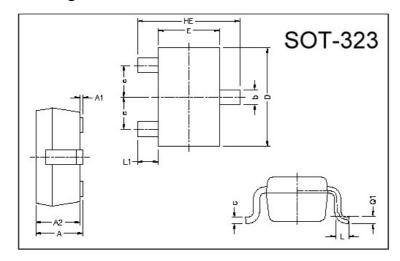
GS411SD

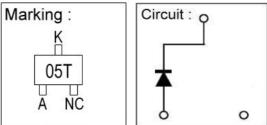
SURFACE MOUNT, SCHOTTKY BARRIER DIODE VOLTAGE 40V, CURRENT 0.5A

Description

The GS411SD is designed for low power rectification.

Package Dimensions





REF.	Milli	meter	REF.	Millimeter				
	Min.	Max.	nLI.	Min.	Max.			
Α	0.80	1.10	L1	0.42 REF.				
A1	0	0.10	L	0.15	0.35			
A2	0.80	1.00	b	0.25	0.40			
D	1.80	2.20	С	0.10	0.25			
Е	1.15	1.35	е	0.65 REF.				
HE	1.80	2.40	Q1	0.15 BSC.				

Absolute Maximum Ratings at TA = 25° C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+125	$^{\circ}$ C
Storage Temperature	Tstg	-40 ~ +125	$^{\circ}\mathbb{C}$
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	40	V
Maximum RMS Voltage	V_{RMS}	28	V
Maximum DC Blocking Voltage	V_{DC}	20	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I _{FSM}	3.0	A
Typical Junction Capacitance between Terminal (Note 1)	CJ	20	pF
Maximum Average Forward Rectified Current	lo	0.5	A
Total Power Dissipation	PD	225	mW

Electrical Characteristics (at TA = 25°C unless otherwise noted)

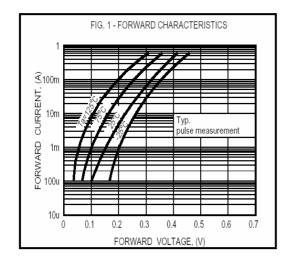
Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions				
Reverse Breakdown Voltage	V(BR)R	40	-	-	V	IR=100μA				
Maximum Instantaneous Forward Voltage	VF	-	-	300	mV	IF1=10mA				
Maximum instantaneous i orward voitage		-	-	500		IF2=500mA				
Maximum Average Reverse Current	lr	-	-	30	uA	VR=10V				

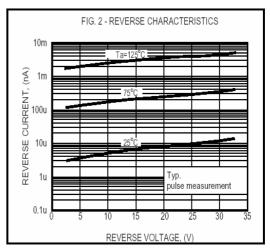
Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 10 volts.

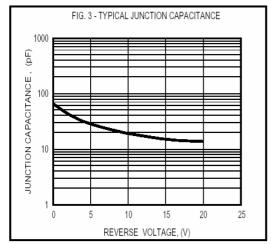
2. ESD sensitive product handling required.

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Characteristics Curve







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